

Method and Aparatus for Reducing Fixed Charge in Semiconductor Device Layers

Abstract of the Disclosure

- 5 The fixed charge in a borophosphosilicate glass insulating film deposited on a semiconductor device is reduced by reacting an organic precursor such as TEOS with O_3 . When done at temperatures higher than approximately 480 degrees C, the carbon level in the resulting film appears to be reduced, resulting in a higher threshold voltage for field transistor devices.

"Express Mail" mailing label number: EV298565225US

Date of Deposit: December 4, 2003

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to the Commissioner for Patents, Mail Stop Patent Application, P.O. Box 1450, Alexandria, VA 22313-1450.